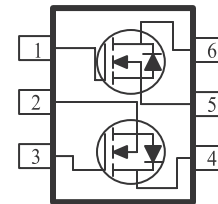
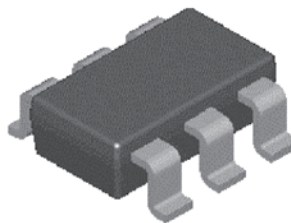


Dual N-Channel Logic Level MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are logic switch control, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature TSOP-6 Surface Mount Package Saves Board Space
- Very fast switching
- Gate to Source Zener Diode ESD Protect



PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (OHM)	I_D (A)
25	0.45 @ $V_{GS} = 4.5$ V	0.5
	0.63 @ $V_{GS} = 2.5$ V	0.2

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	25	V
Gate-Source Voltage		V_{GS}	8	
Continuous Drain Current ^a	$T_A = 25^\circ\text{C}$	I_D	0.7	A
	$T_A = 70^\circ\text{C}$		0.58	
Pulsed Drain Current ^b		I_{DM}	2	
Continuous Source Current (Diode Conduction) ^a		I_S	± 0.3	A
Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	0.9	W
	$T_A = 70^\circ\text{C}$		0.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{THJA}	140	$^\circ\text{C/W}$
	Steady-State		180	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	25			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	0.67	0.85	1.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^{\circ}\text{C}$			10	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 2.5\text{ V}$	0.5			A
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 0.5\text{ A}$		0.33	0.45	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 0.5\text{ A}, T_J = 55^{\circ}\text{C}$		0.36	0.49	
		$V_{GS} = 2.5\text{ V}, I_D = 0.2\text{ A}$		0.45	0.63	
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 5\text{ V}, I_D = 0.5\text{ A}$		1.5		S
Diode Forward Voltage	V_{SD}	$I_S = 0.5\text{ A}, V_{GS} = 0\text{ V}$		0.85	1.20	V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 5\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.5\text{ A}$		1.7	2.3	nC
Gate-Source Charge	Q_{gs}			0.38	0.72	
Gate-Drain Charge	Q_{gd}			0.47	0.87	
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\text{ V}, I_D = 0.5\text{ A},$ $V_{GEN} = 4.5\text{ V}, R_G = 50\text{ }\Omega$		6.5	13	ns
Rise Time	t_r			11	19	
Turn-Off Delay Time	$t_{d(off)}$			13	24	
Fall-Time	t_f			3	7	

Notes

- Pulse test: $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

Typical Electrical Characteristics

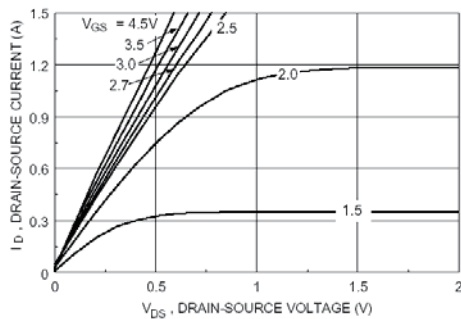


Figure 1. On-Region Characteristics

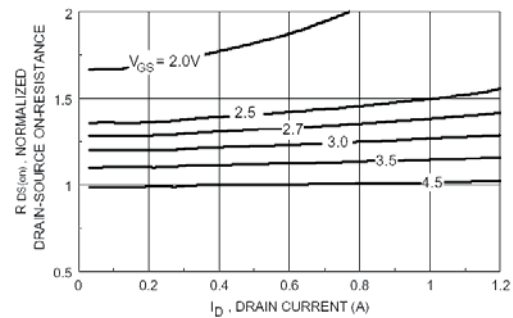


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

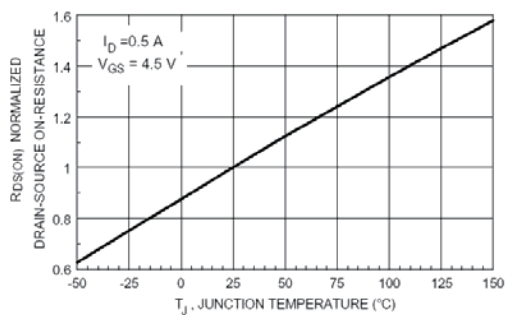


Figure 3. On-Resistance Variation with Temperature

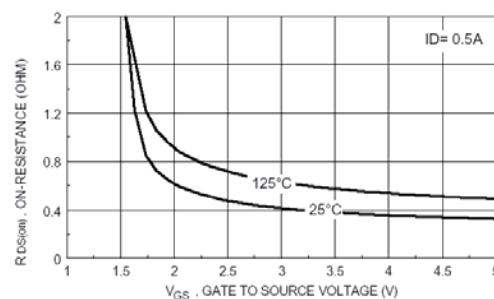


Figure 4. On-Resistance Variation with Gate to Source Voltage

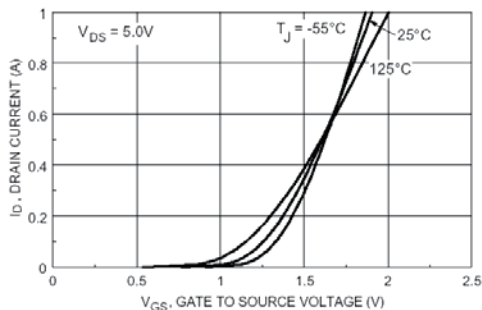


Figure 5. Transfer Characteristics

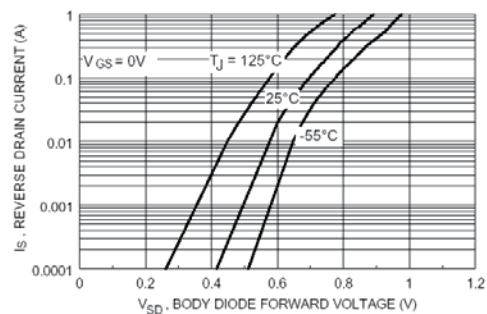


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics

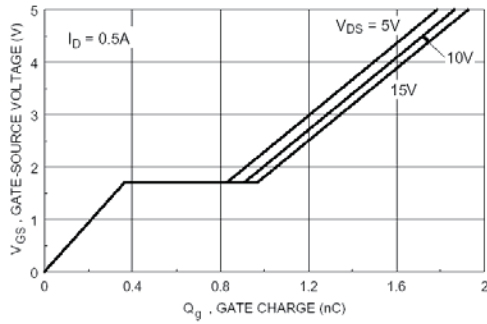


Figure 7. Gate Charge Characteristics.

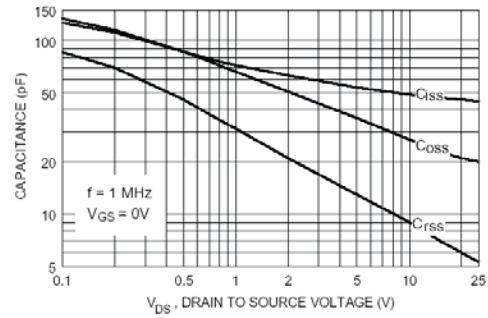


Figure 8. Capacitance Characteristics.

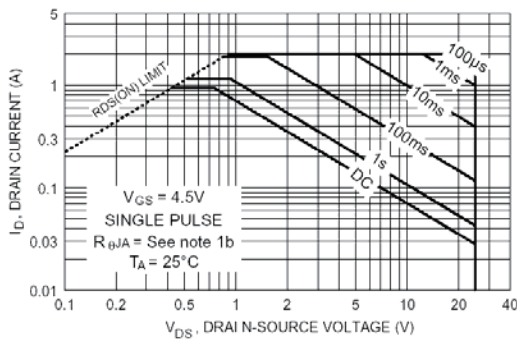


Figure 9. Maximum Safe Operating Area

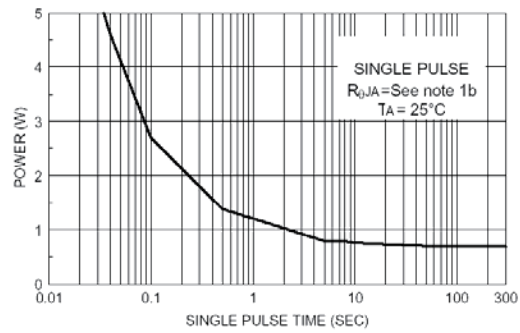


Figure 10. Single Pulse Maximum Power
Dissipation

Normalized Thermal Transient Junction to Ambient

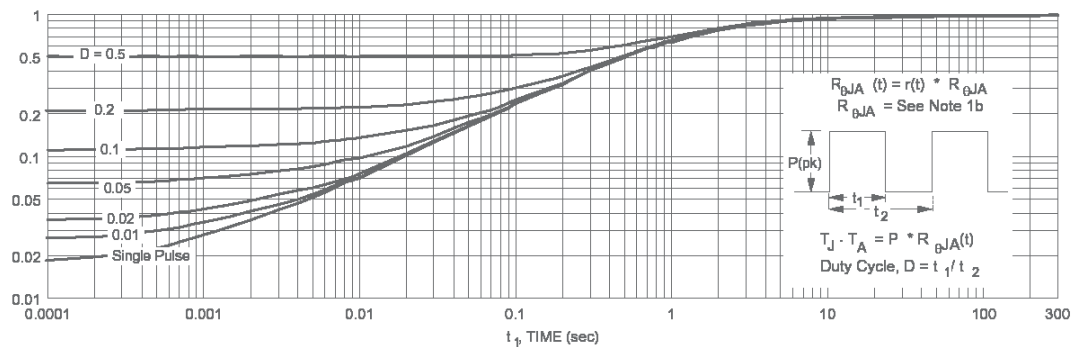
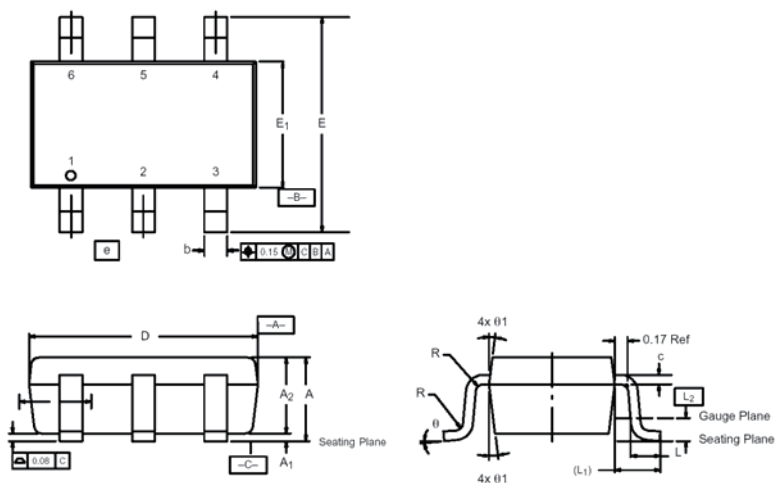


Figure 11. Transient Thermal Response Curve

Package Information

TSOP-6: 6LEAD



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	—	1.10	0.036	—	0.043
A ₁	0.01	—	0.10	0.0004	—	0.004
A ₂	0.84	—	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
L	0.35	—	0.50	0.014	—	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	—	—	0.004	—	—
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		